

DESCRIPTION

The IS281 series optocoupler consists of an infrared emitting diode optically coupled to an NPN silicon photo transistor.

This device belongs to Isocom Compact Range of Optocouplers.

FEATURES

- Half Pitch 1.27mm
- High AC Isolation voltage 3750V_{RMS}
- CTR Selections Available
- Wide Operating Temperature Range -55°C to 110°C
- Pb Free and RoHS Compliant
- UL Approval E91231, Model "THP"

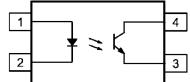
APPLICATIONS

- Switching Mode Power Supply
- Industrial System Controllers
- Measuring Instruments
- Signal Transmission between Systems of Different Potentials and Impedances

ORDER INFORMATION

 Available in Tape and Reel with 1000pcs per reel





- 1 Anode
- 2 Cathode
- 3 Emitter
- 4 Collector

ABSOLUTE MAXIMUM RATINGS $(T_A = 25^{\circ}C)$

Stresses exceeding the absolute maximum ratings can cause permanent damage to the device.

Exposure to absolute maximum ratings for long periods of time can adversely affect reliability.

Input

Forward Current	50mA
Reverse Voltage	6V
Power dissipation	70mW

Output

Collector to Emitter Voltage BV _{CEO}	80V
Emitter to Collector Voltage BV _{ECO}	7V
Collector Current	50mA
Power Dissipation	150mW

Total Package

Isolation Voltage	$3750V_{RMS}$
Total Power Dissipation	200mW
Operating Temperature	-55 to 110 °C
Storage Temperature	-55 to 150 °C
Lead Soldering Temperature	260°C
(10s)	

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ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise specified)

INPUT

Parameter	Symbol	Test Condition	Min	Тур.	Max	Unit
Forward Voltage	V_{F}	$I_F = 20 \text{mA}$		1.2	1.4	V
Reverse Current	I_R	$V_R = 4V$			10	μΑ
Terminal Capacitance	C_{IN}	V = 0V, $f = 1KHz$		30	250	pF

OUTPUT

Parameter	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_C = 0.1 \text{mA}, I_F = 0 \text{ mA}$	80			V
Emitter-Collector Breakdown Voltage	$\mathrm{BV}_{\mathrm{ECO}}$	$I_E = 0.1 \text{mA}, I_F = 0 \text{mA}$	7			V
Collector-Emitter Dark Current	I_{CEO}	$V_{CE} = 20V$, $I_F = 0mA$			100	nA



ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise specified)

COUPLED

Parameter	Symbol	Test Condition	Min	Тур.	Max	Unit
Current transfer ratio	CTR	$I_F = 5 \text{mA}, V_{CE} = 5 \text{V}$				%
		IS281	50		600	
		IS281A	80		160	
		IS281B	130		260	
		IS281C	200		400	
		IS281D	300		600	
		IS281E	100		200	
		IS281F	150		300	
		IS281GB	100		600	
		$I_F = 10 \text{mA}, V_{CE} = 5 \text{V}$				
		IS281H	40		80	
		IS281I	63		125	
		IS281J	100		200	
		IS281K	160		320	
		IS281GR	100		300	
Collector-Emitter Saturation Voltage	V _{CE(sat)}	$I_F = 10 \text{mA}, I_C = 1 \text{mA}$		0.1	0.2	V
Floating Capacitance	C_{f}	$V_F = 0V, f = 1MHz$ 0.3		pF		
Output Rise Time	t _r	$V_{CE} = 2V$, $Ic = 2mA$, $R_L = 100\Omega$		6	18	μs
Output Fall Time	t_{f}	$V_{CE} = 2V, Ic = 2mA,$ $R_{L} = 100\Omega$ 6 18		μs		

ISOLATION

Parameter	Symbol	Test Condition	Min	Тур.	Max	Unit
Isolation Voltage	$V_{\rm ISO}$	R.H. = 40% to 60%, t = 1 min Note 1	3750			V_{RMS}
Input - Output Resistance	$R_{\text{I-O}}$	$V_{I-O} = 500 VDC$ R.H. = 40% to 60% Note 1	5x10 ¹⁰			Ω

Note 1: Measured with input leads shorted together and output leads shorted together.



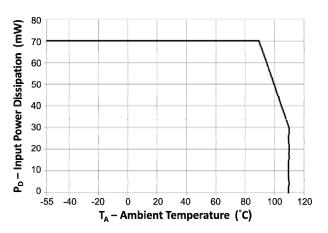


Fig 1 Input Power Dissipation vs Ambient Temperature

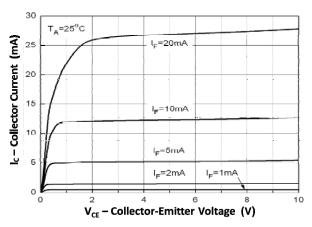


Fig 3 Collector Current vs Collector-Emitter Voltage (1)

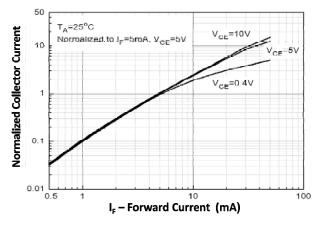


Fig 5 Normalized Collector Current vs Forward Voltage

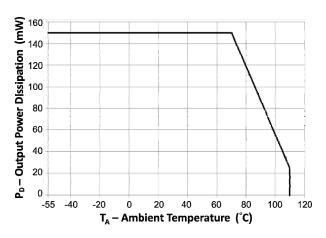


Fig 2 Output Power Dissipation vs Ambient Temperature

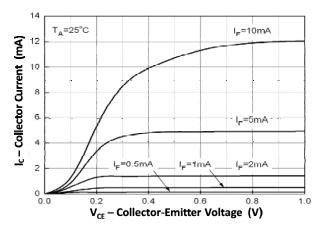


Fig 4 Collector Current vs Collector-Emitter Voltage (2)

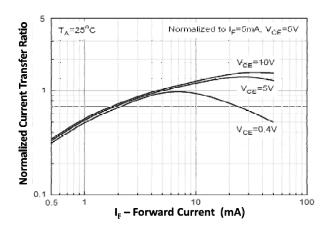


Fig 6 Collector Current Transfer Ratio vs Forward Current



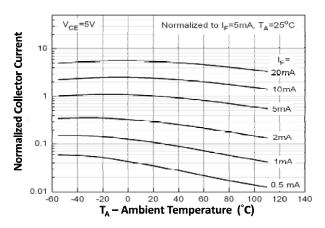


Fig 7 Normalized Collector Current vs Ambient Temperature

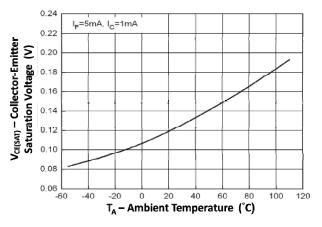


Fig 9 Collector-Emitter Voltage vs Ambient Temperature

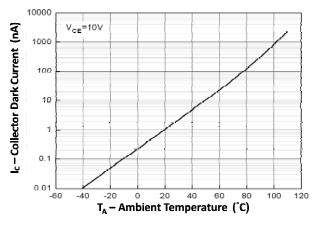


Fig 11 Collector Dark Current vs Ambient Temperature

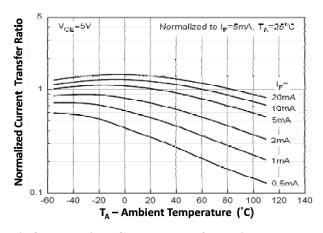


Fig 8 Normalized Current Transfer Ratio vs Ambient Temperature

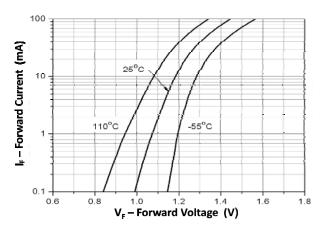


Fig 10 Forward Current vs Forward Voltage



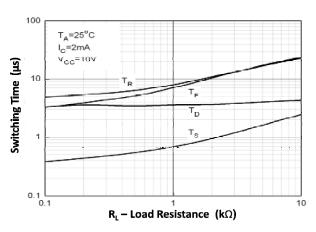
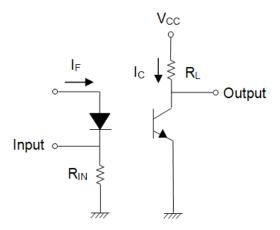
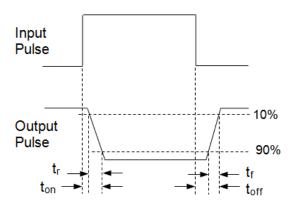


Fig 12 Switching Time vs Load Resistance





Switching Time Test Circuit



ORDER INFORMATION

IS281				
After PN	PN	Description	Packing quantity	
None	IS281	Surface Mount Tape & Reel	1000 pcs per reel	
Any CTR Grade	IS281A, IS281B, IS281C, IS281D, IS281E, IS281F, IS281H, IS281I, IS281J, IS281K, IS281GR, IS281GB	Surface Mount Tape & Reel	1000 pcs per reel	

NOTE: Multiple Grades may be supplied to meet the requested specification

DEVICE MARKING



THP_ denotes Device Part Number where "_" denotes CTR Grade

I denotes Isocom

Y denotes 1 digit Year code

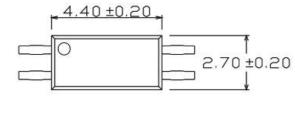
WW denotes 2 digit Week code

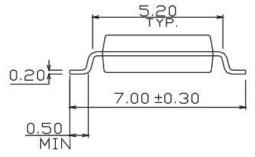
Note: Device Optional Marking

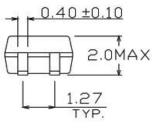
IS281 THP1
IS281B THP3
IS281F THP10



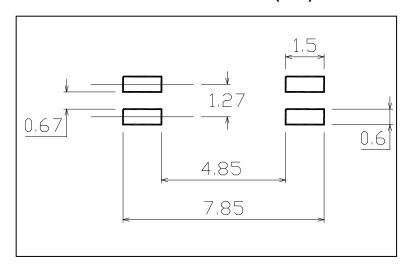
PACKAGE DIMENSIONS (mm)





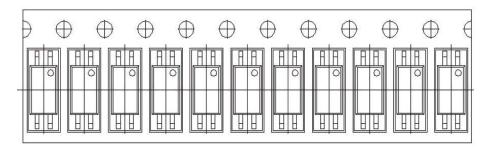


RECOMMENDED SOLDER PAD LAYOUT (mm)



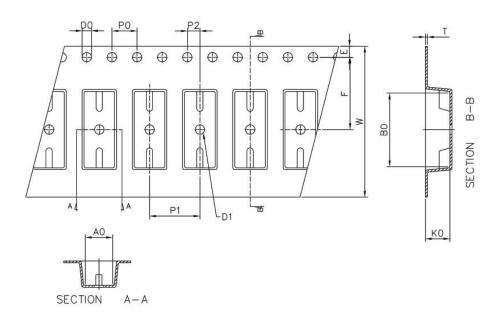


Tape and Reel Packaging





Direction of feed from reel

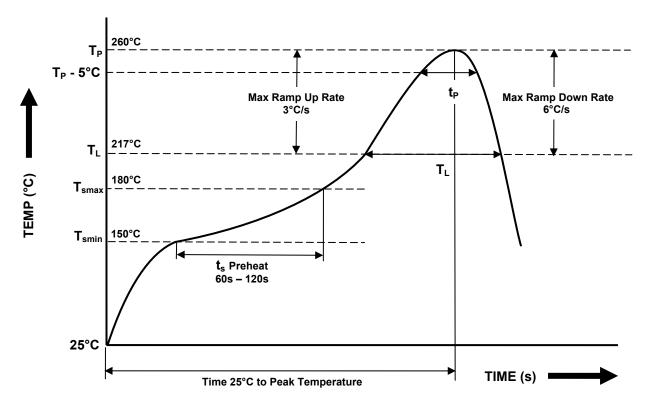


Dimension No.	Α0	В0	D0	D1	E	F
Dimension(mm)	3.00±0.10	7.45±0.10	1.50+0.1/-0	1.50±0.10	1.75±0.10	5.5±0.10
Dimension No.	P0	P1	P2	t	w	K0
Dimension (mm)	4.00±0.15	4.00±0.10	2.00±0.10	0.30±0.05	12.1±0.2	2.45±0.1



IR REFLOW SOLDERING TEMPERATURE PROFILE

One Time Reflow Soldering is Recommended. Do not immerse device body in solder paste.



Profile Details	Conditions
$ \begin{array}{l} \textbf{Preheat} \\ \textbf{- Min Temperature } (T_{SMIN}) \\ \textbf{- Max Temperature } (T_{SMAX}) \\ \textbf{- Time } T_{SMIN} \text{ to } T_{SMAX} \left(t_s\right) \end{array} $	150°C 180°C 60s - 120s
$\begin{tabular}{lll} \textbf{Soldering Zone} \\ - & \mbox{Peak Temperature } (T_P) \\ - & \mbox{Liquidous Temperature } (T_L) \\ - & \mbox{Time within } 5^{\circ}\mbox{C of Actual Peak Temperature } (T_P = 5^{\circ}\mbox{C}) \\ - & \mbox{Time maintained above } T_L \ (t_L) \\ - & \mbox{Ramp Up Rate } (T_L \ \mbox{to } T_P) \\ - & \mbox{Ramp Down Rate } (T_P \ \mbox{to } T_L) \\ \end{tabular}$	260°C 217°C 20s 60s 3°C/s max 3 - 6°C/s
Average Ramp Up Rate (T _{smax} to T _P)	3°C/s max
Time 25°C to Peak Temperature	8 minutes max



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